

# Electron-photon and electron-electron scattering as dephasing mechanisms in a single quantum emitter

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Offen im Denken



H. Mannel<sup>1</sup>, M. Zöllner<sup>1</sup>, F. Rimek<sup>1</sup>, J. Kerski<sup>1</sup>, A. Ludwig<sup>2</sup>, A. D. Wieck<sup>2</sup>, P. Lochner<sup>1</sup>, A. Kurzmann<sup>1,3</sup>, A. Lorke<sup>1</sup>, M. Geller<sup>1</sup>

<sup>1</sup>Faculty of Physics and CENIDE, University of Duisburg-Essen, Lotharstr. 1, 47057 Duisburg, Germany

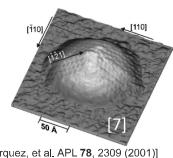
<sup>2</sup>Chair of Applied Solid State Physics, Ruhr-Universität Bochum, Universitätsstr. 150, 44780 Bochum, Germany

<sup>3</sup>2nd Institute of Physics, RWTH Aachen University, Otto-Blumenthal-Str. 18, 52074 Aachen, Germany

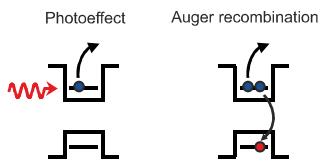
## 1. Motivation

Excitons in semiconductor quantum dots (QDs)

- Promising candidate for quantum information technologies
- Resonance fluorescence** (RF) is ideal: No generation of electrons/holes in the environment; less dephasing



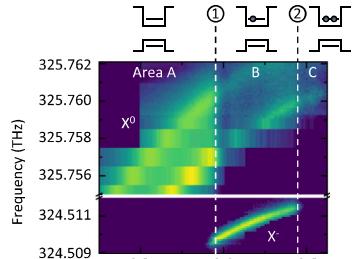
[Márquez, et al. APL 78, 2309 (2001)]



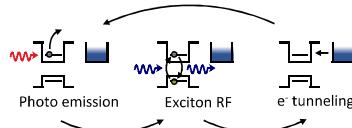
- Dephasing mechanisms** besides spin and charge noise [1]:
- Electron-photon scattering: Electron emission into the conduction band by the **photoeffect** [2,3]
  - Electron-electron scattering, e.g. **Auger recombination** of the trion [4-6]

## 3. Electron-photon scattering - The photoeffect [2,3]

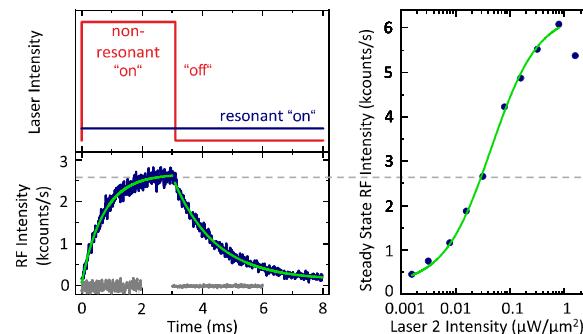
- Resonance fluorescence intensity of the exciton  $X^0$  and trion  $X^-$  transition:



- Schematic representation of the photoemission effect which allows to excite the  $X_0$  in area B of the trion transition:



- Time-resolved two-laser resonant excitation:
  - Non-resonant in the band gap (photoeffect)
  - Resonant on the exiton transition (read-out)

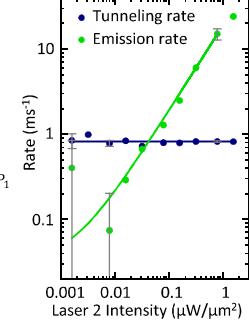


- Non-resonant laser 2 "on": Increasing exciton intensity by the photoeffect
- Non-resonant laser 2 "off": Electron tunneling quenches the  $X^0$

- The tunneling and electron emission rate (by the electron-photon scattering) can be obtained by using a rate equation:

$$\text{Tunneling rate } \gamma_{In} = (0.82 \pm 0.02) \text{ ms}^{-1}$$

$$\text{Emission rate } \gamma_{Emission} = [(18.8 \pm 0.3) \cdot I_{Laser}] \text{ ms}^{-1} \mu\text{W}/\mu\text{m}^2$$



- Rate equations:

$$P_0 = \gamma_{In} P_0 + \gamma_{Emission} P_1$$

$$P_0 + P_1 = 1$$

$$P_0(0) = 0$$

$P_0 \triangleq$  QD unoccupied

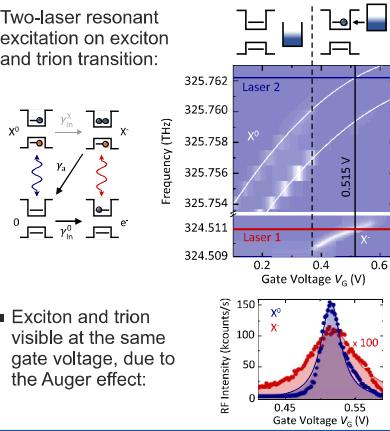
$P_1 \triangleq$  QD occupied with 1 electron

- The maximum steady-state intensity of the  $X^0$  increases with the non-resonant laser 2 excitation

$$P_0(t) = \frac{\gamma_{Emission}}{\gamma_{In} + \gamma_{Emission}} (1 - \exp(-(\gamma_{In} + \gamma_{Emission})t))$$

## 5. Electron-electron scattering - The Auger effect [4-6]

- Two-laser resonant excitation on exciton and trion transition:



- Exciton and trion visible at the same gate voltage, due to the Auger effect:

- Electron tunneling vs. the Auger recombination
  - Excitation on the trion transition: Auger effect
  - Excitation on the exciton transition: Electron tunneling into the dot

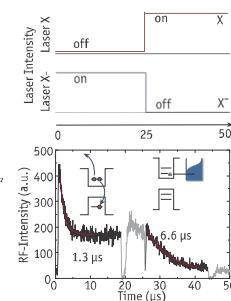
- Rate equation yields:  
Probability for the fluorescent trion state:

$$P_f(t) = \frac{\gamma_{In} + n\gamma_a e^{-\gamma_a t}}{\gamma_{In} + n\gamma_a}$$

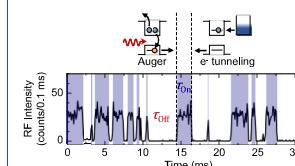
Relaxation rate:  $\gamma_m = \gamma_{In} + n\gamma_a$

Tunneling rate:  $\gamma_{In} = 0.2 \mu\text{s}^{-1}$

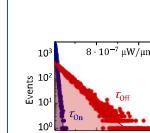
Auger rate:  $\gamma_a = 2.3 \mu\text{s}^{-1}$



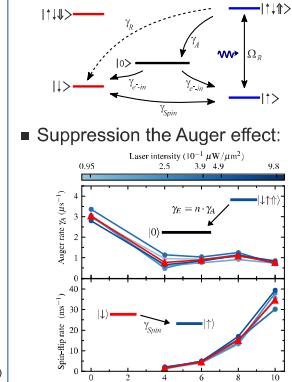
- Real-time measurement of every Auger recombination event:



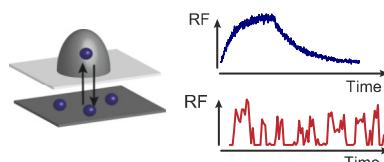
- Waiting time distribution:



- In a magnetic field:



## 6. Conclusion



Two important dephasing mechanisms, even in resonant excitation of a quantum emitter:

- The internal photoeffect can emit an electron/hole from the conduction/band into the continuum
- The Auger effect as an electron-electron scattering event that has a negative influence on the trion
- Suppression by magnetic field or band structure engineering (reduction of the final states in the continuum)

## Further reading

[1] Kuhlmann et al., Nature Phys. **9**, 570 (2013).

[2] Kurzmann et al., Nano Lett. **16**, 3367 (2016).

[3] Lochner et al., Nano Lett. **20**, 1631 (2020).

[4] Kurzmann et al., Appl. Phys. Lett. **108**, 263108 (2016).

[5] Lochner et al., Phys. Rev. B **103**, 075426 (2021).

[6] Mannel et al., preprint: arXiv:2110.12213 (2021).

contact: martin.geller@uni-due.de